

Listing of claims:

1. **(Previously presented)** A composition for the production of semiconductors, comprising H₂SiF₆ and/or HBF₄ in a total amount of 10-500 mg/kg, 12-17% by weight of H₂SO₄, 2-4% by weight of H₂O₂, optionally in combination with additives, in aqueous solution.
2. **(Currently amended)** A process for residual polymer removal from a semiconductor surface comprising contacting a semiconductor surface with a composition comprising H₂SiF₆ and/or HBF₄ with the structured semiconductor surface in order to remove residual polymers from the structured semiconductor surface.
3. **(Previously presented)** A process according to claim 2 for the removal of residual polymers from Al or Al-containing conductor tracks on said semiconductor surface.
4. **(Previously presented)** A process according to claim 2 for the removal of residual polymers after dry etching on metal conductor tracks and contact holes on said semiconductor surface.
5. **(Previously presented)** A process for the removal of residual polymers from aluminum or copper/aluminum alloys a comprising contacting a semiconductor surface having aluminum or copper/aluminum alloys with a composition according to claim 1.
6. **(Previously presented)** A process for residual polymer removal from a semiconductor surface comprising contacting a semiconductor surface with a composition comprising H₂SiF₆ and/or HBF₄ in a total amount of 10-500 mg/kg, 12-17% by weight of H₂SO₄, 2-4% by weight of H₂O₂, optionally in combination with

additives, in aqueous solution.

7. **(Currently amended)** A process according to claim 2 further comprising contacting a semiconductor surface with a composition comprising H₂SiF₆ and/or HBF₄⁻ in a spin etcher or in a tank unit.

8. **(Previously presented)** A process for the removal of residual polymers from Al or Al-containing conductor tracks, wherein residual polymers are removed using a composition according to claim 1.

9.-10. **(Cancelled)**

11. **(Previously presented)** A process according to claim 6, for the removal of residual polymers after dry etching on metal conductor tracks and contact holes on said semiconductor surface.

12. **(New)** A composition for the production of semiconductors, comprising H₂SiF₆ and/or HBF₄ in a total amount of 10-500 mg/kg, 1-17% by weight of H₂SO₄, 1-15% by weight of H₂O₂, optionally in combination with additives, in aqueous solution.

13. **(New)** A process for the removal of residual polymers from aluminum or copper/aluminum alloys comprising contacting a semiconductor surface having aluminum or copper/aluminum alloys with a composition according to claim 12.

14. **(New)** The process of claim 2, wherein said composition further comprises HBF₄.